



PJM08C40PA

N and P-Channel Complementary Power MOSFET

Product Summary

- **N-Channel**
- $V_{DS} = 40V, I_D = 8A$
- $R_{DS(on)} < 19m\Omega @ V_{GS} = 10V$
- $R_{DS(on)} < 29m\Omega @ V_{GS} = 4.5V$
- **P-Channel**
- $V_{DS} = -40V, I_D = -7A$
- $R_{DS(on)} < 35m\Omega @ V_{GS} = -10V$
- $R_{DS(on)} < 45m\Omega @ V_{GS} = -4.5V$

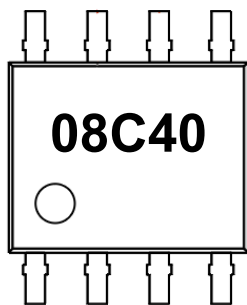
Features

- Advanced Trench Technology
- 100% Avalanche Tested
- RoHS and Reach Compliant
- Halogen and Antimony Free
- Moisture Sensitivity Level 3

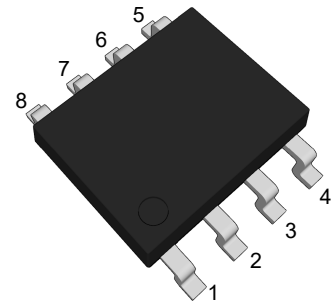
Application

- Power Management

Marking Code



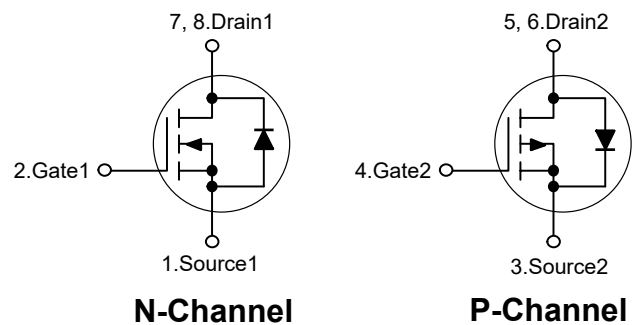
SOP-8



(Top View)

Pin	Description	Pin	Description
1	Source1	4	Gate2
2	Gate1	5,6	Drain2
3	Source2	7,8	Drain1

Schematic Diagram





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Absolute Maximum Ratings

Ratings at 25°C ambient temperature unless otherwise specified.

Parameter	Symbol	N-Channel	P-Channel	Unit
Drain-Source Voltage	V_{DS}	40	-40	V
Gate-Source Voltage	V_{GS}	± 20		V
Drain Current-Continuous	I_D	8	-7	A
Drain Current-Pulsed ^{Note1}	I_{DM}	40	-30	A
Maximum Power Dissipation	P_D	2		W
Junction Temperature	T_J	150		°C
Storage Temperature Range	T_{STG}	-55 to +150		°C

Thermal Characteristics

Thermal Resistance,Junction-to-Ambient ^{Note2}	$R_{\theta JA}$	62.5	62.5	°C/W
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PJM08C30PA

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N-Channel

Electrical Characteristics

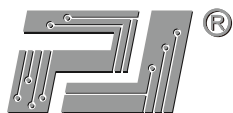
($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =250μA	40	--	--	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =40V, V _{GS} =0V	--	--	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	--	--	±100	nA
Gate Threshold Voltage ^{Note3}	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1	1.5	2	V
Drain-Source On-Resistance ^{Note3}	R _{DS(on)}	V _{GS} =10V, I _D =8A	--	14	19	mΩ
		V _{GS} =10V, I _D =4A	--	19	29	mΩ
Forward Transconductance ^{Note3}	g _{FS}	V _{DS} =5V, I _D =8A	33	--	--	S
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{DS} =20V, V _{GS} =0V, f=1MHz	--	415	--	pF
Output Capacitance	C _{oss}		--	112	--	pF
Reverse Transfer Capacitance	C _{rss}		--	11	--	pF
Total Gate Charge	Q _g	V _{DS} =20V, I _D =8A, V _{GS} =10V	--	12	--	nC
Gate-Source Charge	Q _{gs}		--	3.2	--	nC
Gate-Drain Charge	Q _{gd}		--	3.1	--	nC
Switching Characteristics						
Turn-on Delay Time	t _{d(on)}	V _{DD} =15V, R _L =2.5Ω V _{GS} =10V, R _{GEN} =3Ω	--	4	--	nS
Turn-on Rise Time	t _r		--	3	--	nS
Turn-off Delay Time	t _{d(off)}		--	15	--	nS
Turn-off Fall Time	t _f		--	2	--	nS
Source-Drain Diode Characteristics						
Diode Forward Voltage ^{Note3}	V _{SD}	V _{GS} =0V, I _S =8A	--	0.8	1.2	V
Diode Forward Current ^{Note2}	I _S		--	--	8	A

Note: 1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2.Surface Mounted on FR4 Board, $t \leq 10$ sec.

3.Pulse Test: Pulse width $\leq 300\mu s$, duty cycles $\leq 2\%$



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Electrical Characteristics

($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$-V_{(BR)DSS}$	$V_{GS}=0V, I_D=-250\mu A$	40	--	--	V
Zero Gate Voltage Drain Current	$-I_{DSS}$	$V_{DS}=-40V, V_{GS}=0V$	--	--	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	--	--	± 100	nA
Gate Threshold Voltage ^{Note3}	$-V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	1	1.5	2	V
Drain-Source On-Resistance ^{Note3}	$R_{DS(on)}$	$V_{GS}=-10V, I_D=-8A$	--	29	35	m Ω
		$V_{GS}=-4.5V, I_D=-4A$	--	34	45	m Ω
Forward Transconductance ^{Note3}	g_{FS}	$V_{DS}=-5V, I_D=-8A$	10	--	--	S
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS}=-20V, V_{GS}=0V, f=1MHz$	--	520	--	pF
Output Capacitance	C_{oss}		--	100	--	pF
Reverse Transfer Capacitance	C_{rss}		--	65	--	pF
Total Gate Charge	Q_g	$V_{DS}=-20V, I_D=-8A, V_{GS}=-10V$	--	13	--	nC
Gate-Source Charge	Q_{gs}		--	3.8	--	nC
Gate-Drain Charge	Q_{gd}		--	3.1	--	nC
Switching Characteristics						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=-20V, R_L=2.3\Omega$ $V_{GS}=-10V, R_{GEN}=6\Omega$	--	7.5	--	nS
Turn-on Rise Time	t_r		--	5.5	--	nS
Turn-off Delay Time	$t_{d(off)}$		--	19	--	nS
Turn-off Fall Time	t_f		--	7	--	nS
Source-Drain Diode Characteristics						
Diode Forward Voltage ^{Note3}	$-V_{SD}$	$V_{GS}=0V, I_S=-7A$	--	--	1.2	V
Diode Forward Current ^{Note2}	$-I_S$		--	--	7	A

Note: 1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2.Surface Mounted on FR4 Board, $t \leq 10$ sec.

3.Pulse Test: Pulse width $\leq 300\mu s$, duty cycles $\leq 2\%$

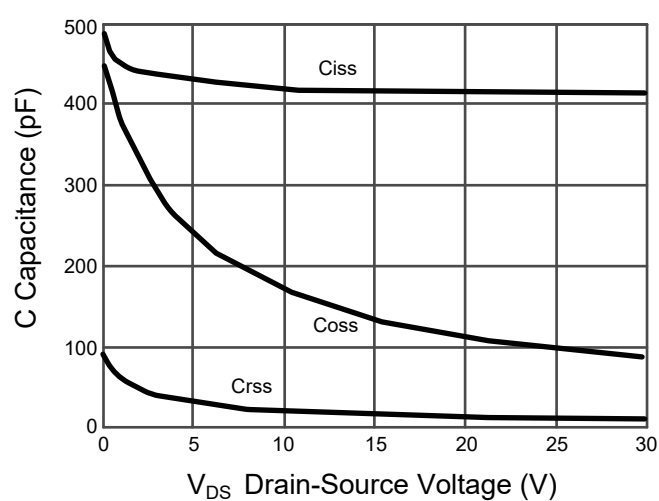
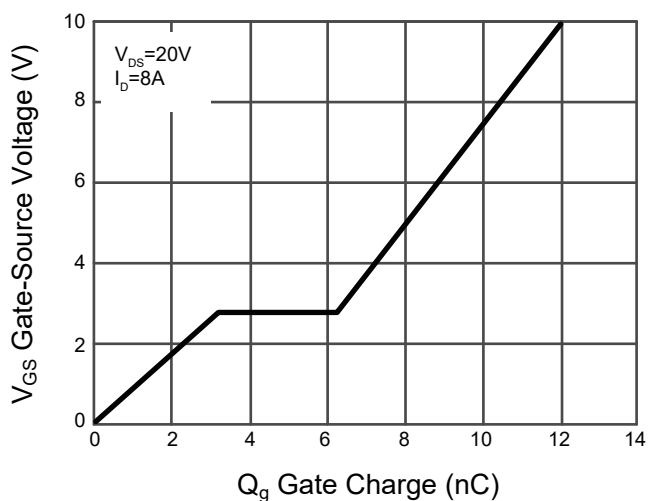
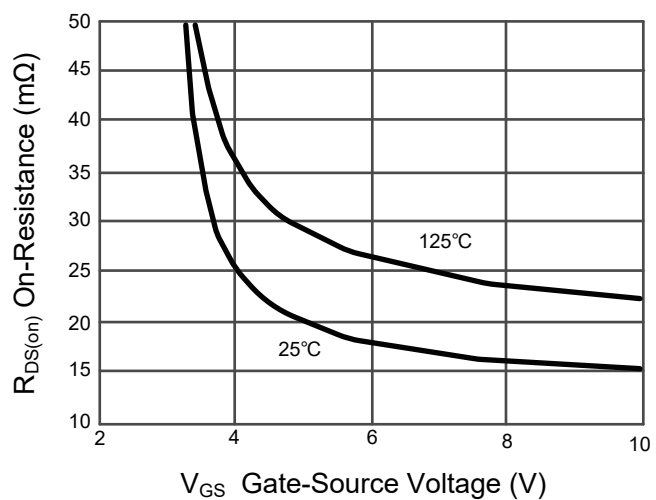
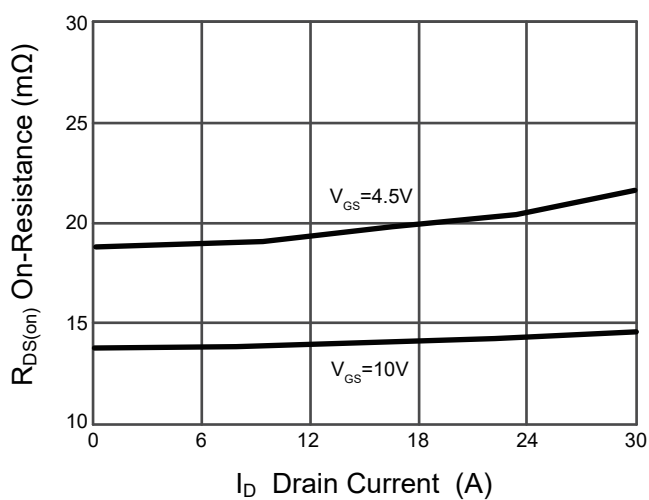
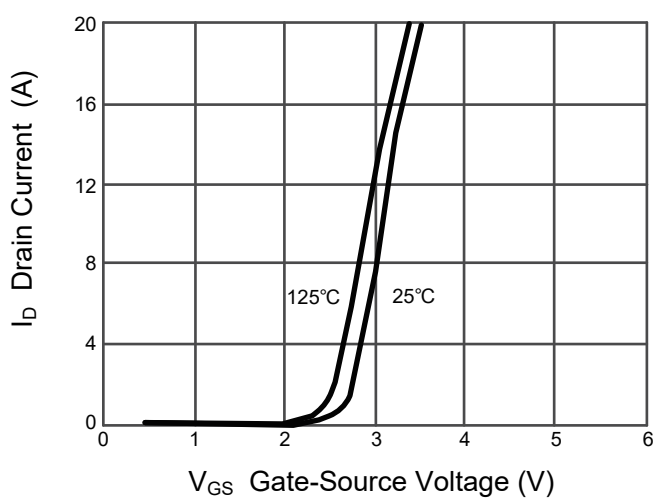
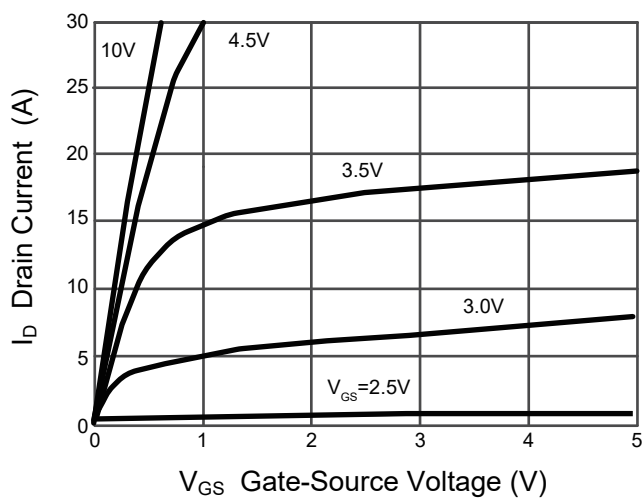


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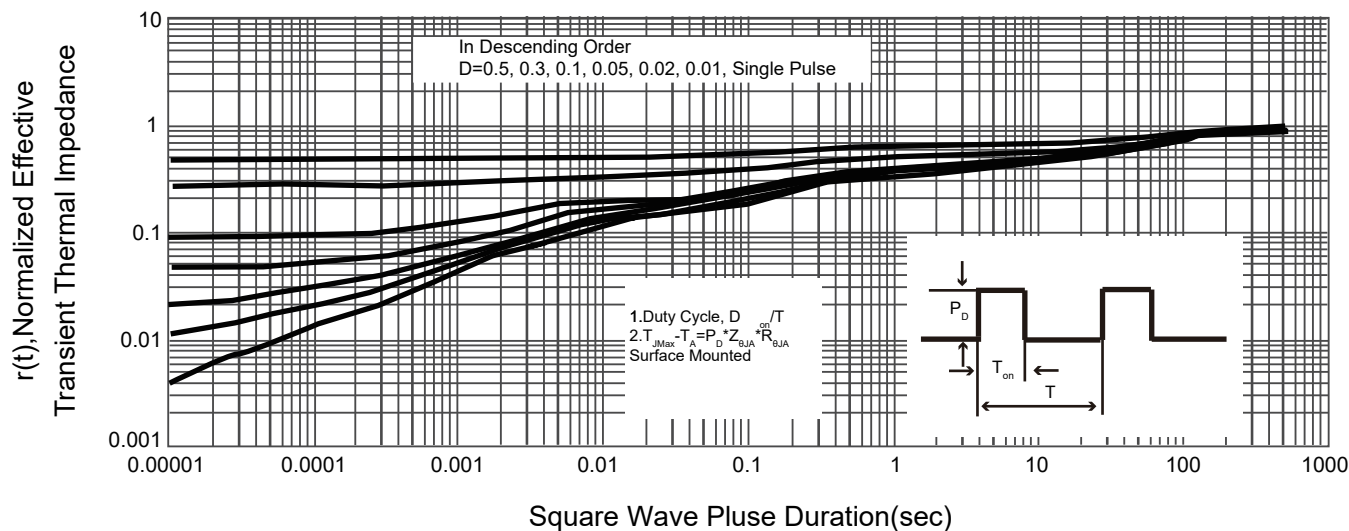
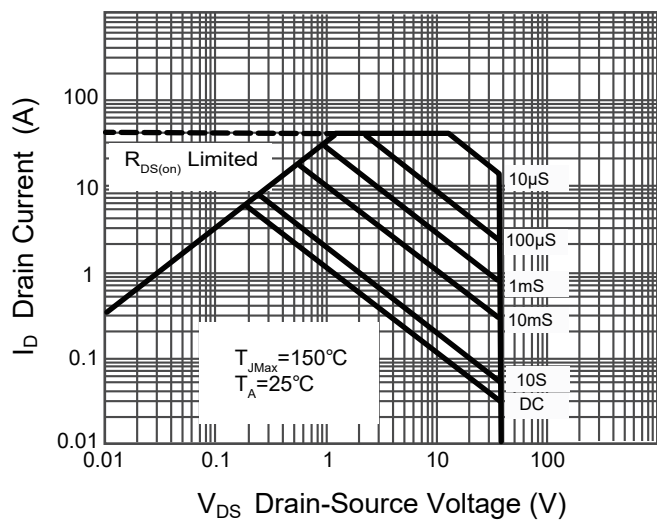
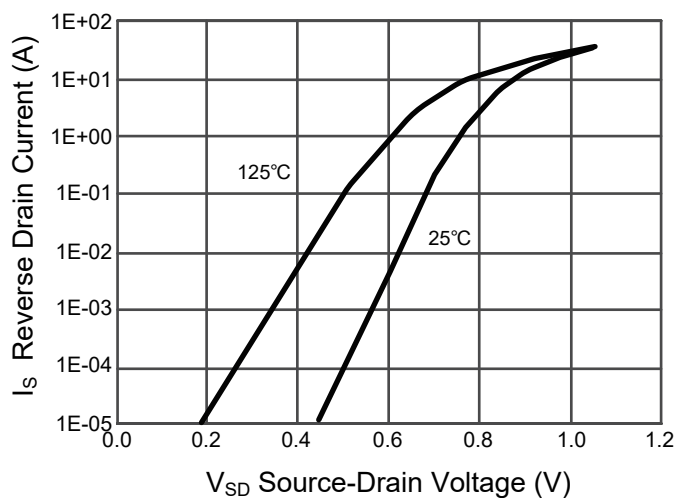
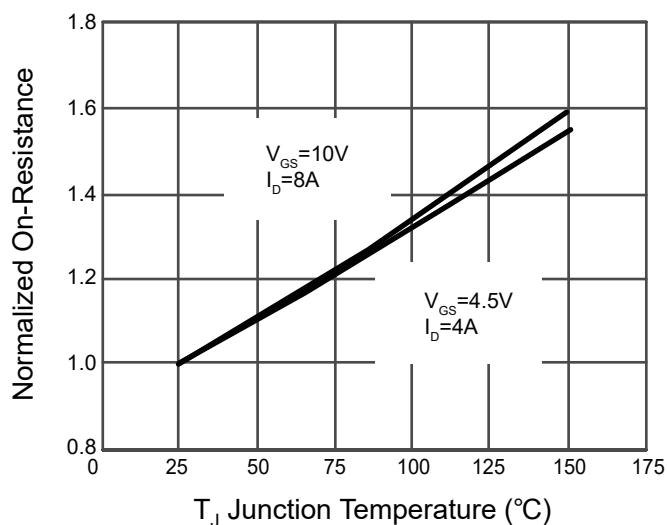
Typical Characteristics Curves





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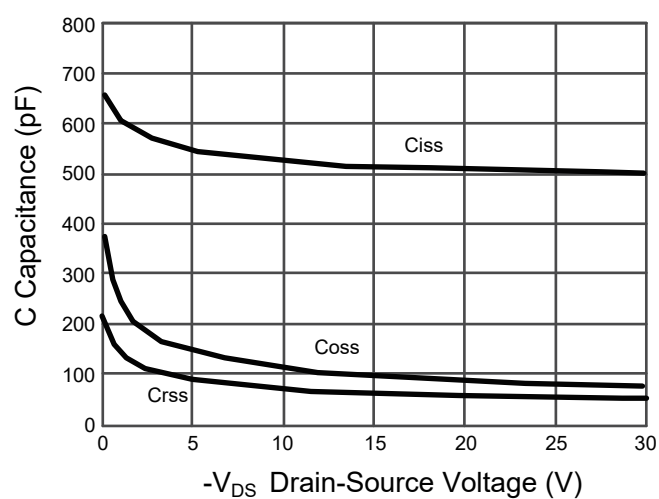
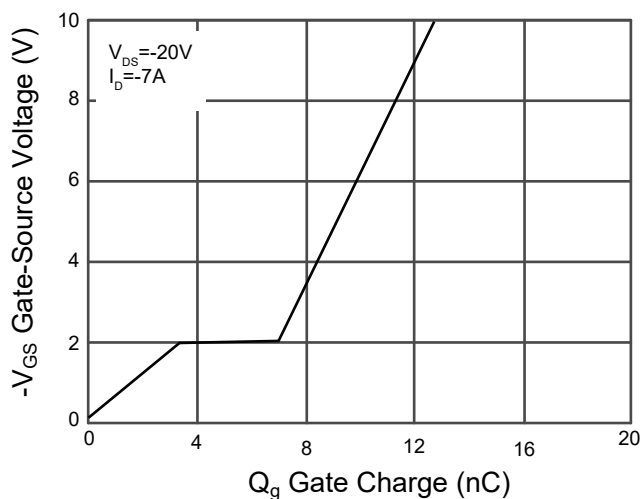
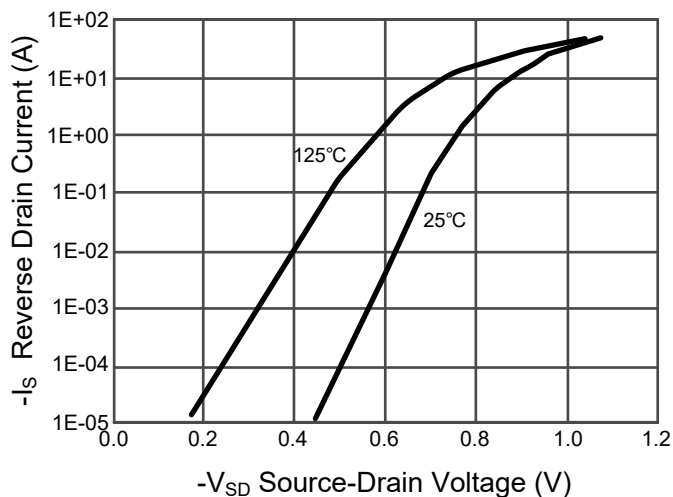
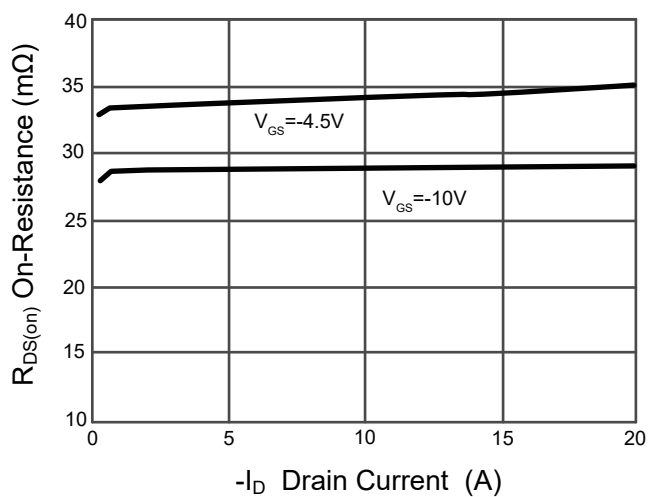
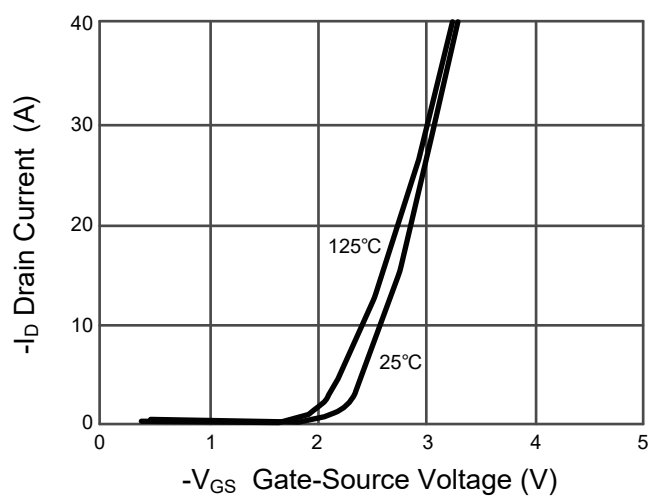
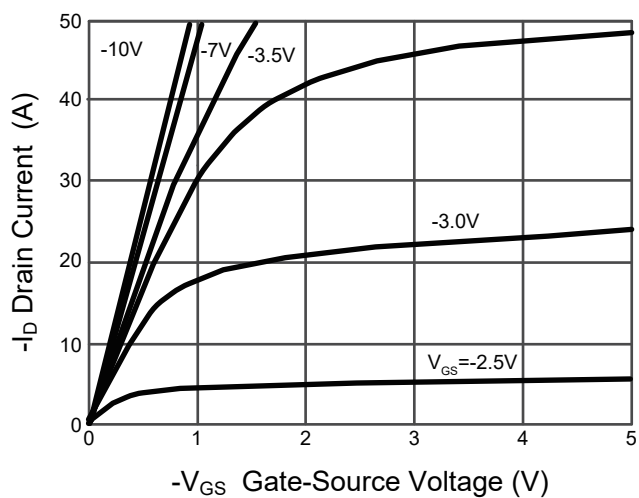


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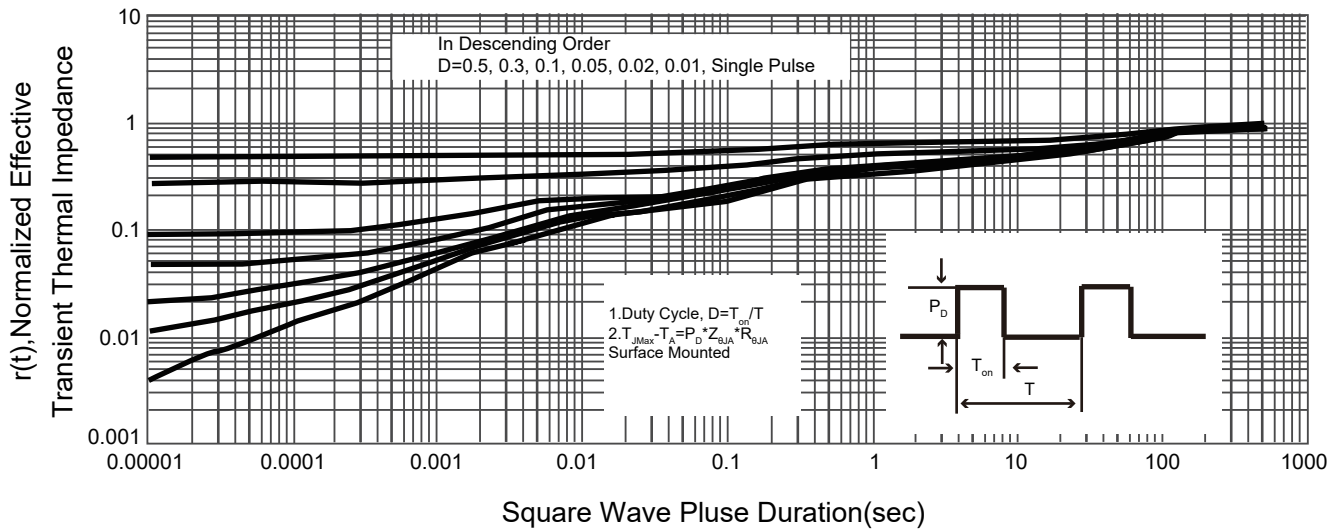
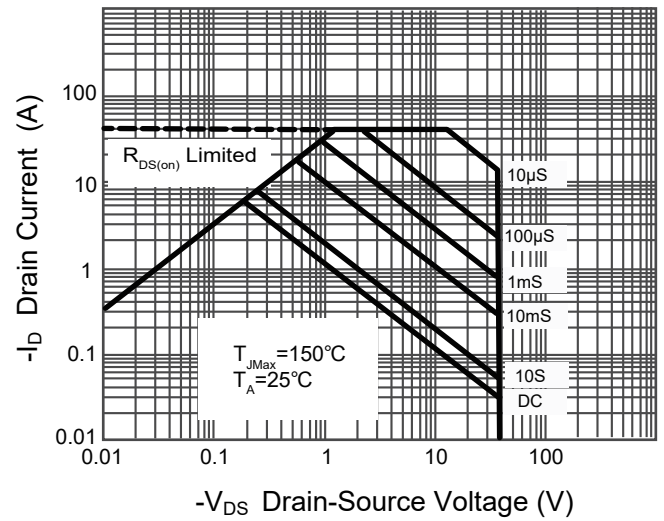
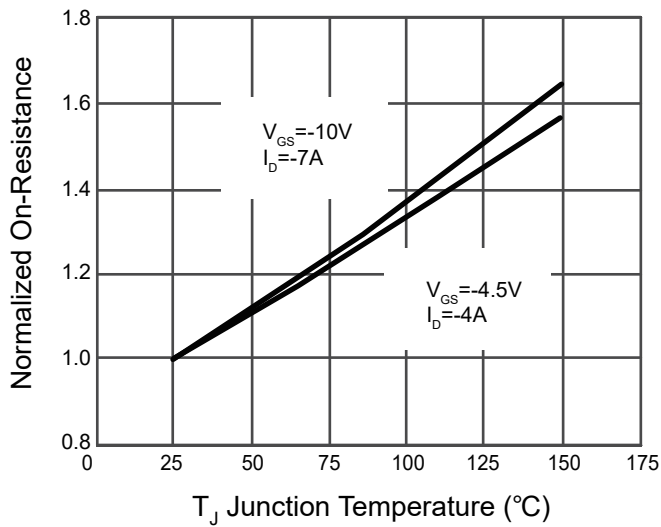
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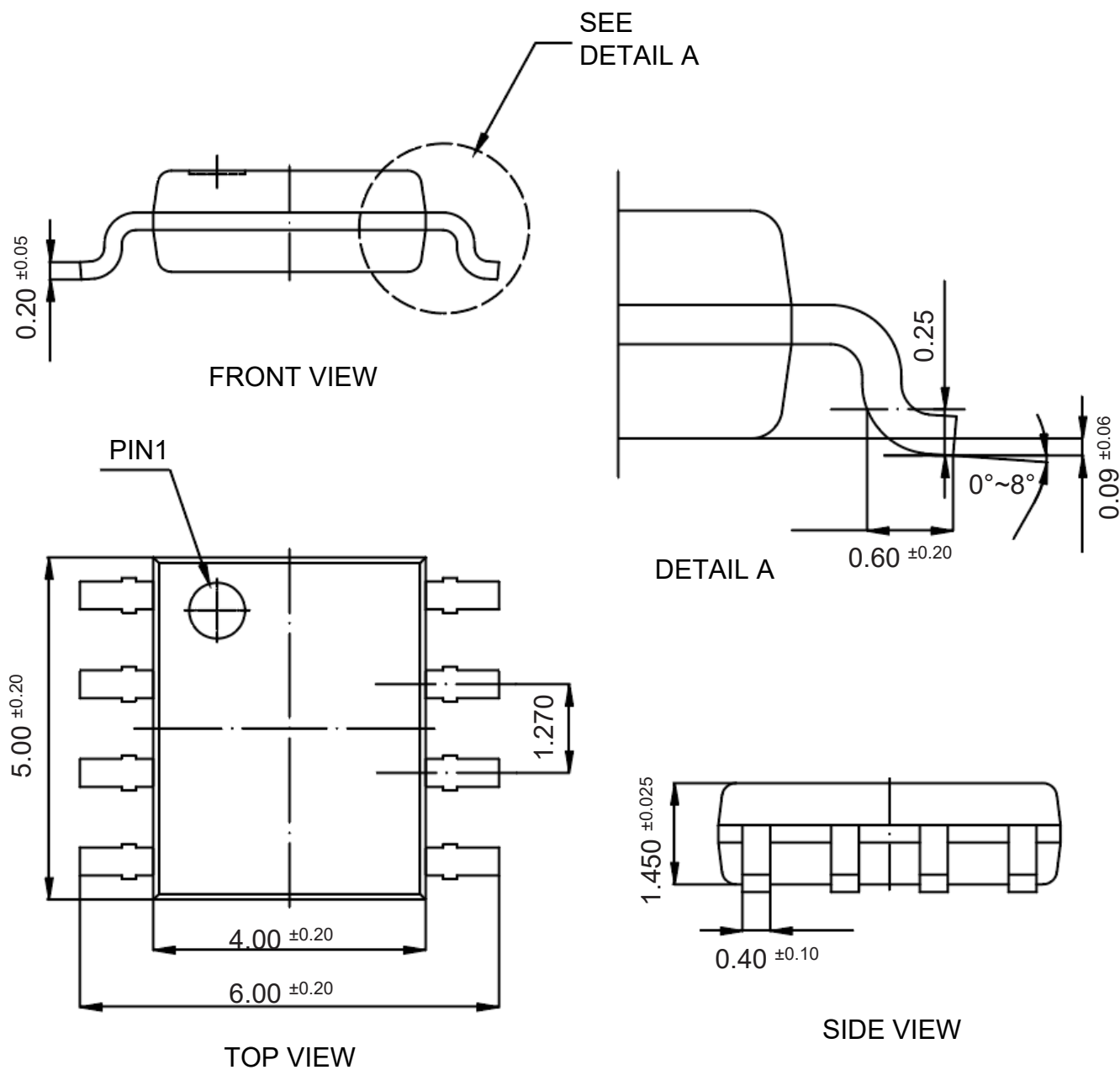
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Package Outline

SOP-8

Dimensions in mm



Ordering Information

Device	Package	Shipping
PJM08C40PA	SOP-8	4,000PCS/Reel&13inches